



**DGD2104M** 

#### HALF-BRIDGE GATE DRIVER IN SO-8

#### Description

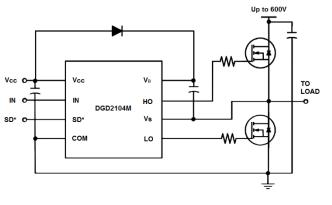
The DGD2104M is a high-voltage / high-speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half bridge configuration. High-voltage processing techniques enable the DGD2104M's high side to switch to 600V in a bootstrap operation.

The DGD2104M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high-pulse current buffers designed for minimum driver cross conduction.

The DGD2104M is offered in the SO-8 package and operates over an extended -40°C to +125°C temperature range.

### Applications

- DC-DC Converters
- DC-AC Inverters
- AC-DC Power Supplies
- Motor Controls
- Class D Power Amplifiers



Typical Configuration

# Features

- Floating High-Side Driver in Bootstrap Operation to 600V
- Drives Two N-Channel MOSFETs or IGBTs in a Half Bridge Configuration
- 290mA Source / 600mA Sink Output Current Capability
- Designed for Enhanced Performance in Noisy Motor Applications
- Outputs Tolerant to Negative Transients
- Internal Dead Time to Protect MOSFETs
- Wide Low-Side Gate Driver Supply Voltage: 10V to 20V
- Logic Input (IN and SD\*) 3.3V Capability
- Schmitt Triggered Logic Inputs
- Undervoltage Lockout for V<sub>CC</sub> (Logic and Low Side Supply)
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

- Case: SO-8 (Type TH)
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads
  Solderable per MIL-STD-202, Method 208 (9)
- Weight: 0.074 grams (Approximate)

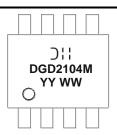


### Ordering Information (Note 4)

F	Part Number	Marking	Reel Size (inch)	Tape Width (mm)	Quantity per Reel
DG	D2104MS8-13	DGD2104M	13	12	2,500
Notes:	1. No purposely adde	ed lead. Fully EU Directive 2002/9	5/EC (RoHS), 2011/65/EU (RoHS	2) & 2015/863/EU (RoHS 3) com	pliant.

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

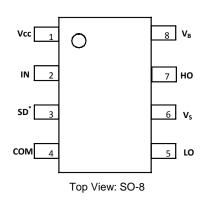
### **Marking Information**



)¦¦ = Manufacturer's Marking DGD2104M = Product Type Marking Code YY = Year (ex: 19 = 2019) WW = Week (01 to 53)



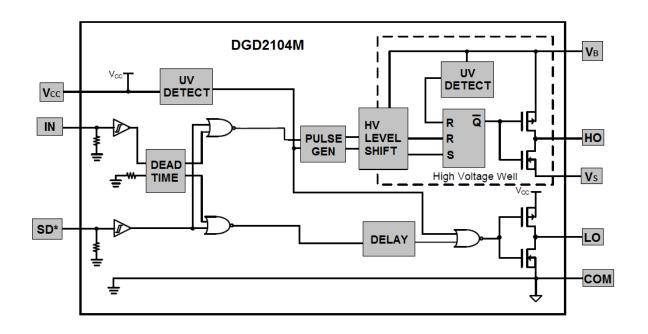
# Pin Diagrams



## **Pin Descriptions**

Pin Number	Pin Name	Function
1	V <sub>CC</sub>	Logic and Low Side Supply
2	IN	Logic Input for High-Side and Low-Side Gate Driver Outputs (HO and LO), in Phase with HO
3	SD*	Logic input for Shutdown, Enabled Low
4	COM	Low-Side and Logic Return
5	LO	Low-Side Gate Drive Output
6	Vs	High-Side Floating Supply Return
7	HO	High-Side Gate Drive Output
8	VB	High-Side Floating Supply

# **Functional Block Diagram**





#### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Supply Voltage	VB	-0.3 to +624	V
High-Side Floating Supply Offset Voltage	Vs	V <sub>B</sub> -24 to V <sub>B</sub> +0.3	V
High-Side Floating Output Voltage	V <sub>HO</sub>	V <sub>S</sub> -0.3 to V <sub>B</sub> +0.3	V
Offset Supply Voltage Transient	dVs / dt	50	V/ns
Low-Side Fixed Supply Voltage	V <sub>CC</sub>	-0.3 to +24	V
Low-Side Output Voltage	V <sub>LO</sub>	-0.3 to V <sub>CC</sub> +0.3	V
Logic Input Voltage (IN and SD*)	V <sub>IN</sub>	-0.3 to V <sub>CC</sub> +0.3	V

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	PD	0.625	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	200	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	TL	+300	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

### **Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
High Side Floating Supply Absolute Voltage	VB	V <sub>S</sub> + 10	V <sub>S</sub> + 20	V
High Side Floating Supply Offset Voltage	Vs	(Note 6)	600	V
High Side Floating Output Voltage	V <sub>HO</sub>	Vs	VB	V
Low Side Fixed Supply Voltage	Vcc	10	20	V
Low Side Output Voltage	V <sub>LO</sub>	0	V <sub>CC</sub>	V
Logic Input Voltage (IN and SD*)	V <sub>IN</sub>	0	5	V
Ambient Temperature	T <sub>A</sub>	-40	+125	°C

Note: 6. Logic operation for Vs of -5V to +600V.



#### **DC Electrical Characteristics** (V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, @T<sub>A</sub> = +25°C, unless otherwise specified.) (Note 7)

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Logic "1" (IN) & Logic "0" (SD*) Input Voltage (Note 8)	VIH	2.5	_	-	V	$V_{CC} = 10V$ to 20V
Logic "0" (IN) & Logic "1" (SD*) Input Voltage (Note 8)	VIL	_	-	0.8	V	$V_{CC} = 10V$ to 20V
High Level Output Voltage, V <sub>BIAS</sub> - V <sub>O</sub>	V <sub>OH</sub>	_	0.05	0.2	V	$I_0 = 2mA$
Low Level Output Voltage, Vo	Vol	_	0.02	0.1	V	$I_0 = 2mA$
Offset Supply Leakage Current	I <sub>LK</sub>	—	-	50	μA	$V_B = V_S = 600V$
Quiescent V <sub>BS</sub> Supply Current	I <sub>BSQ</sub>	—	60	100	μA	$V_{IN} = 0V \text{ or } 5V$
Quiescent V <sub>CC</sub> Supply Current	ICCQ1	-	350	500	μA	$V_{IN} = 0V \text{ or } 5V, SD^* = 5V$
Quiescent V <sub>CC</sub> Supply Current in Shutdown	I <sub>CCQ2</sub>	—	590	750	μA	$V_{IN} = 0V \text{ or } 5V, SD^* = 0V$
Logic "1" Input Bias Current	I <sub>IN+</sub>	—	3.0	10	μA	$V_{IN} = 5V, SD^* = 0V$
Logic "0" Input Bias Current	I <sub>IN-</sub>	—	-	5.0	μA	$V_{IN} = 0V, SD^* = 5V$
V <sub>CC</sub> Supply Undervoltage Positive Going Threshold	V <sub>CCUV+</sub>	8.0	8.9	9.8	V	—
V <sub>CC</sub> Supply Undervoltage Negative Going Threshold	Vccuv-	7.4	8.2	9.0	V	—
V <sub>BS</sub> Supply Undervoltage Positive Going Threshold	V <sub>BSUV+</sub>	4.5	5.5	6.5	V	—
V <sub>BS</sub> Supply Undervoltage Negative Going Threshold	V <sub>BSUV-</sub>	4.2	5.2	6.2	V	-
Output High Short Circuit Pulsed Current	I <sub>O+</sub>	130	290	_	mA	V <sub>O</sub> = 0V, PW ≤ 10µs
Output Low Short Circuit Pulsed Current	I <sub>O-</sub>	270	600	_	mA	V <sub>O</sub> = 15V, PW ≤ 10µs

Notes: 7. The V<sub>IN</sub> and I<sub>IN</sub> parameters are applicable to the two logic pins: IN and SD\*. The V<sub>O</sub> and I<sub>O</sub> parameters are applicable to the respective output pins: HO and LO.

8. For optimal operation, it is recommended that the input pulses (IN and SD\*) should have an minimum amplitude of 2.5V with a minimum pulse width of 840ns.

# AC Electrical Characteristics (V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, C<sub>L</sub> = 1000pF, @T<sub>A</sub> = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Тур	Max	Unit	Condition
Turn-On Propagation Delay	t <sub>ON</sub>	-	680	820	ns	$V_{\rm S} = 0V$
Turn-Off Propagation Delay	tOFF	-	150	220	ns	$V_{\rm S} = 600 V$
Shutdown Propagation Delay	t <sub>SD</sub>	-	160	220	ns	-
Delay Matching, HO and LO Turn-On / Turn-Off	t <sub>DM</sub>	-	Ι	60	ns	—
Turn-On Rise Time	t <sub>R</sub>	-	70	170	ns	$V_{\rm S} = 0V$
Turn-Off Fall Time	t <sub>F</sub>	-	35	90	ns	$V_{\rm S} = 0V$
Deadtime: t <sub>DT LO-HO</sub> & t <sub>DT HO-LO</sub>	t <sub>DT</sub>	300	420	650	ns	_



# **Timing Waveforms**

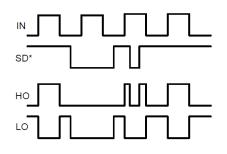


Figure 1. Input / Output Timing Diagram

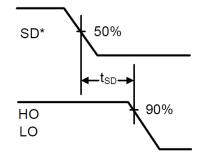
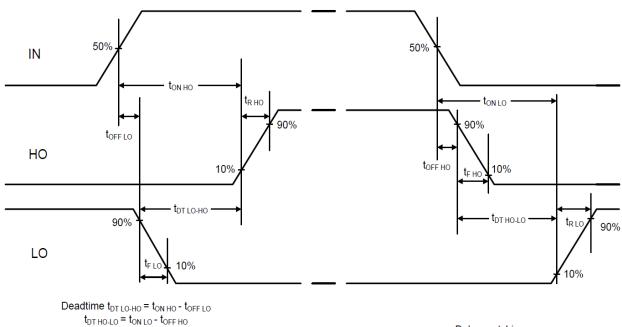
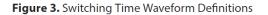


Figure 2. Shutdown Waveform Definition



Deadtime matching t<sub>MDT</sub> = t<sub>DT LO-HO</sub> - t<sub>DT HO-LO</sub>  $\begin{array}{l} \text{Delay matching} \\ t_{\text{DM OFF}} = t_{\text{OFF LO}} - t_{\text{OFF HO}} \\ t_{\text{DM ON}} = t_{\text{ON LO}} - t_{\text{ON HO}} \end{array}$ 





# Typical Performance Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

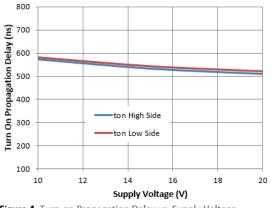


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

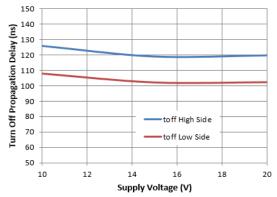
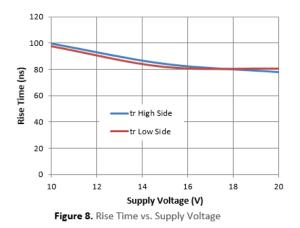


Figure 6. Turn-off Propagation Delay vs. Supply Voltage



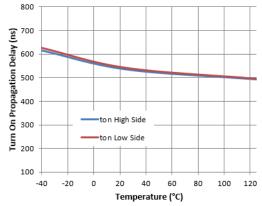


Figure 5. Turn-on Propagation Delay vs. Temperature

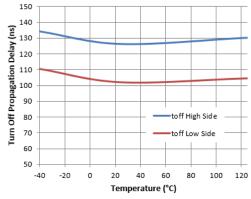
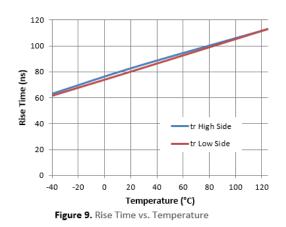
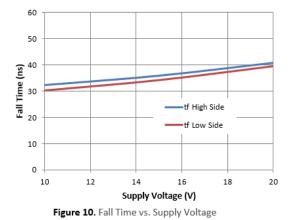


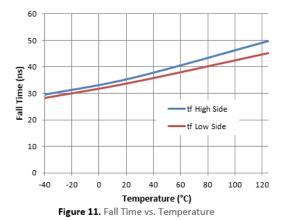
Figure 7. Turn-off Propagation Delay vs. Temperature





# Typical Performance Characteristics (continued)





800 700 •ICC q IBSa 600 Quiescent Current (µA) 500 400 300 200 100 0 12 14 16 18 20 10 Supply Voltage (V)

Figure 12. Quiescent Current vs. Supply Voltage

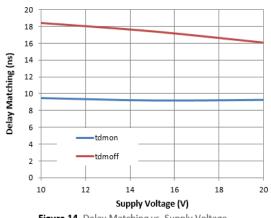
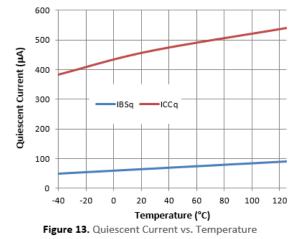


Figure 14. Delay Matching vs. Supply Voltage



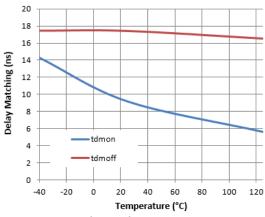
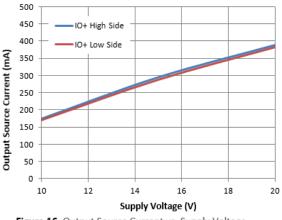


Figure 15. Delay Matching vs. Temperature



# Typical Performance Characteristics (continued)



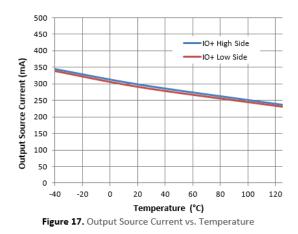
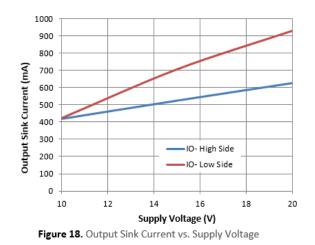


Figure 16. Output Source Current vs. Supply Voltage



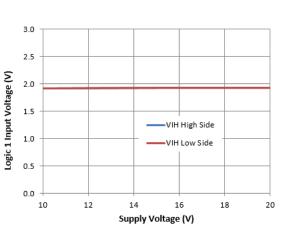
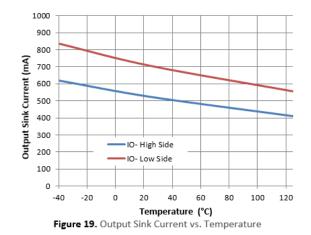


Figure 20. Logic 1 Input Voltage vs. Supply Voltage



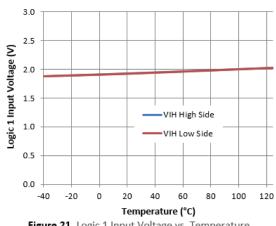
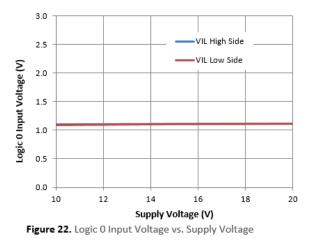


Figure 21. Logic 1 Input Voltage vs. Temperature



# Typical Performance Characteristics (continued)



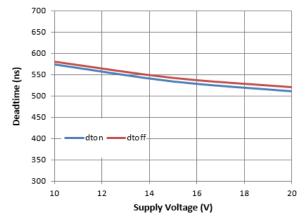
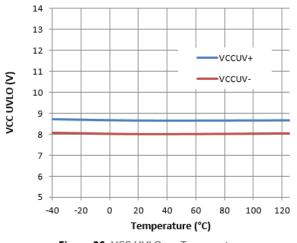


Figure 24. Deadtime vs. Supply Voltage





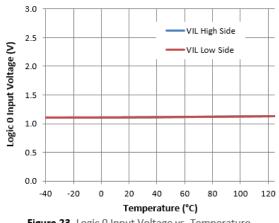


Figure 23. Logic 0 Input Voltage vs. Temperature

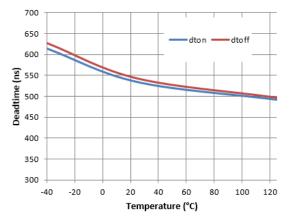


Figure 25. Deadtime vs. Temperature

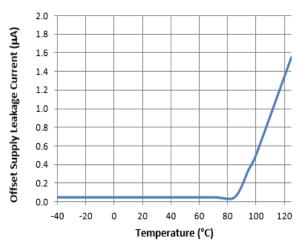


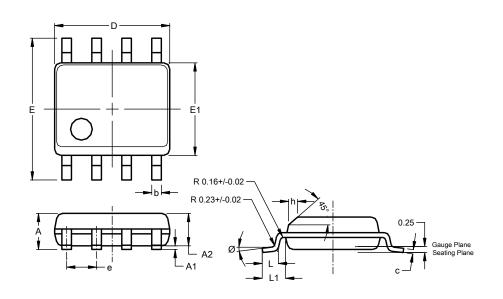
Figure 27. Offset Supply Leakage Current vs. Temperature



DGD2104M

#### **Package Outline Dimensions**

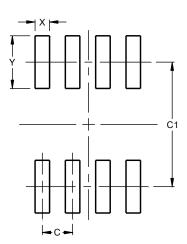
Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8 (Type TH)							
Dim	Min	Max	Тур				
Α	1.35	1.75					
A1	0.10	0.25					
A2	-		1.45				
b	0.35	0.51					
С	0.190	0.248	-				
D	4.80	5.00	4.90				
E	5.80	6.20	6.00				
E1	3.80	4.00	3.90				
е			1.27				
h	0.25	0.50					
L	0.41	1.27					
L1			1.04				
Ø	0°	8°	-				
All Dimensions in mm							

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.27
C1	5.20
Х	0.60
Y	2.20

Note : For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

#### SO-8 (Type TH)

SO-8 (Type TH)



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